

Additional Information





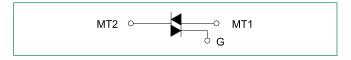


Accessories



Samples

Functional Diagram



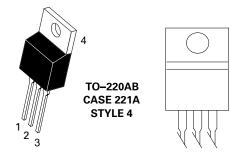
Description

The 2N6394 is designed primarily for half-wave AC control applications, such as motor controls, heating controls and power supplies.

Features

- Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 V
- These are Pb-Free Devices

Pin Out



Maximum Ratings † (TJ = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) $(T_J = -40 \text{ to } 110^{\circ}\text{C}, \text{ Sine Wave, } 50 \text{ to } 60 \text{ Hz, Gate Open})$	2N6394 2N6395 2N6397 2N6399	V _{DRM} ,	50 100 400 800	V
On-State RMS Current (180° Conduction Angles; $T_c = 90$ °C)			12	А
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, T, = 90°C)		I _{TSM}	100	А
Circuit Fusing Considerations (t = 8.3 ms)		l _{2t}	40	A²s
Forward Peak Gate Power (Pulse Width $\leq 1.0 \mu s$, T _C = 90°C)	P_{GM}	20	W	
Forward Average Gate Power (t = 8.3 ms , $T_c = 90^{\circ}\text{C}$)		$P_{G(AV)}$	0.5	W
Forward Peak Gate Current (Pulse Width \leq 1.0 μ s, $T_c = 90$ °C)		I _{GM}	2.0	А
Operating Junction Temperature Range		T _J	-40 to +125	°C
Storage Temperature Range		T _{stg}	-40 to +125	°C

[†]Indicates JEDEC Registered Data

Thermal Characteristics

Rating	Symbol	Value	Unit
† Thermal Resistance, Junction to Case	R _{suc}	2.0	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T,	260	°C

[†] Indicates JEDEC Registered Data.

Electrical Characteristics - OFF (TC = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Тур	Max	Unit
*Peak Repetitive Blocking Current T ₁ = 25°C	I _{DRM} ,	-	-	1.0	μΑ
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$ $T_J = 100^{\circ}$		-	-	2.0	mA

Electrical Characteristics - ON ($TC = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Characteristic		Min	Тур	Max	Unit
†Peak Forward On-State Voltage (Note 2) (I _{TM} = 24 A Peak)	V_{TM}	-	1.7	2.2	V
†Gate Trigger Voltage (Continuous DC), All Quadrants (Continuous dc) ($V_D = 12 \text{ Vdc}$, $R_I = 100 \text{ Ohms}$)		_	5.0	30	mA
†Gate Trigger Voltage (Continuous dc) (V _D = 12 Vdc, R _I = 100 Ohms)		-	0.7	1.5	V
Gate Non-Trigger Voltage ($V_p = 12 \text{ Vdc}$, $R_i = 100 \text{ Ohms}$, $T_j = 125 ^{\circ}\text{C}$)		0.2	_	_	V
†Holding Current ($V_D = 12 \text{ Vdc}$, Initiating Current = 200 mA, Gate Open)		-	6.0	50	mA
Turn-On Time ($I_{TM} = 12 \text{ A}, I_{GT} = 40 \text{ mAdc}, V_D = \text{Rated } V_{DRM}$)		_	1.0	2.0	μs
Turn Off Time (V Peterd V) $(I_{TM} = 12 \text{ A}, I_{R} = 12 \text{ A})$		-	-	15	
Turn-Off Time $(V_D = Rated V_{DRM})$ $(I_{TM} = 12 \text{ A}, I_R = 12 \text{ A}, T_J = 125^{\circ}\text{C})$	L _q	-	-	35	μs

†Indicates JEDEC Registered Data

Pulse Test: Pulse Width ≤ 300 µsec, Duty Cycle ≤ 2%.



Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

^{1.} V_{DRM} and V_{BRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Dynamic Characteristics

Characteristic		Min	Тур	Max	Unit
Critical Rate-of-Rise of Off-State Voltage Expovnential $(V_D = Rated V_{DBM}, T_I = 125^{\circ}C)$	dv/dt(c)	-	50	_	V/µs

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I _L	Holding Current

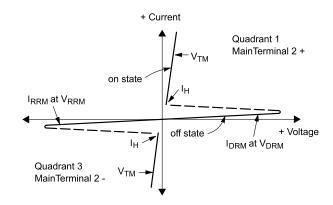


Figure 1. Current Derating

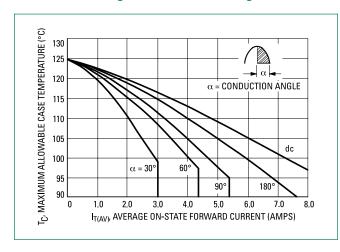


Figure 2. Maximum On-State Characteristics

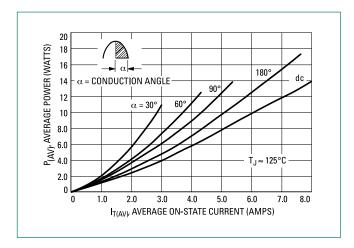


Figure 3. On-State Characteristics

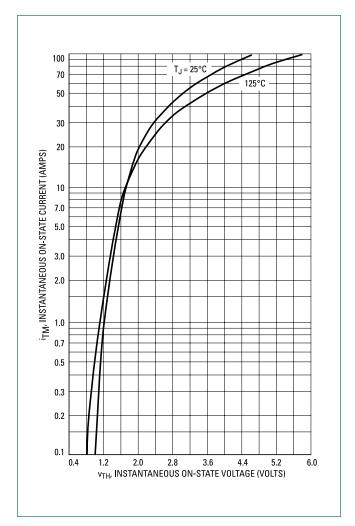


Figure 4. Maximum Non-Repetitive Surge Current

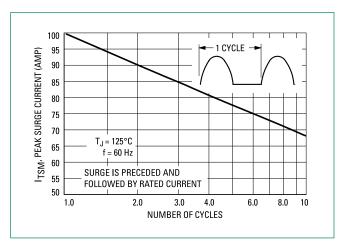
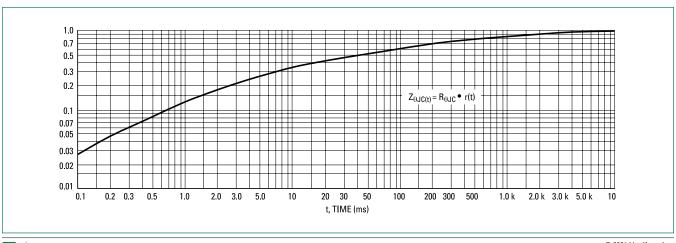


Figure 5. Typical Thermal Response





Typical Characteristics

Figure 6. Typical Gate Trigger Current vs. Pulse Width

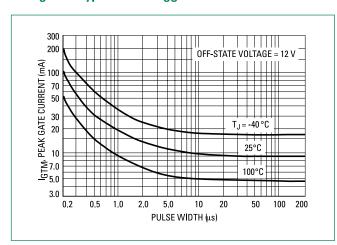


Figure 8. Typical Gate Trigger Voltage vs. Temperature

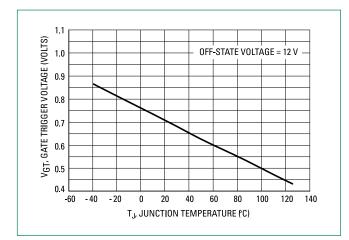


Figure 7. Typical Gate Trigger Current vs. Temperature

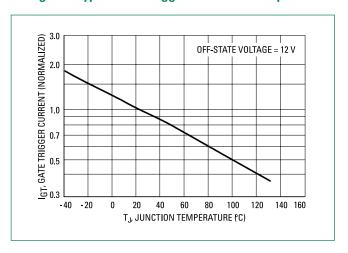
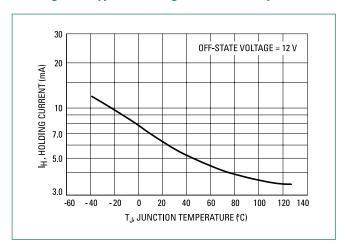


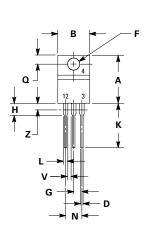
Figure 9. Typical Holding Current vs. Temperature

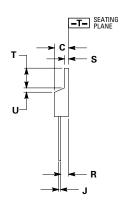


2N6394

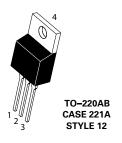
Surface Mount - 50 - 800V

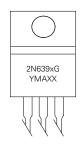
Dimensions





Part Marking System





x =D, M, or N Y =Year

M =Month

A =Assembly Site XX =Lot Serial Code G =Pb-Free Package

D:	Inches		Millim	neters	
Dim	Min	Max	Min	Max	
Α	0.590	0.620	14.99	15.75	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.41	2.67	
Н	0.110	0.130	2.79	3.30	
J	0.018	0.024	0.46	0.61	
K	0.540	0.575	13.72	14.61	
L	0.060	0.075	1.52	1.91	
N	0.195	0.205	4.95	5.21	
Q	0.105	0.115	2.67	2.92	
R	0.085	0.095	2.16	2.41	
S	0.045	0.060	1.14	1.52	
T	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

V	0.045					
Z		0.080				
Dimensioning and tolerancing per ansi y14.5m, 1982. Controlling dimension: inch.						

3. Dimension z defines a zone where all body and lead irregularities are allowed.

Pin Assignment			
1	Cathode		
2	Anode		
3	Gate		
4	Anode		

Ordering Information

Device	Package	Shipping
2N6394G		1000 Units / Box
2N6394TG		1000 Units / Box
2N6395G	TO 000 4 D	1000 Units / Box
2N6397G	TO-220AB (Pb-Free)	1000 Units / Box
2N6397TG	(1 5 1100)	1000 Units / Box
2N6399G		1000 Units / Box
2N6399TG		1000 Units / Box

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